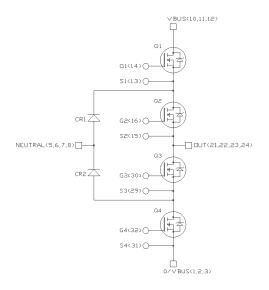
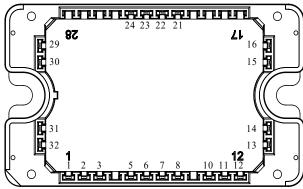
MSCSM120TLM31C3AG

Three Level Inverter SiC MOSFET Power Module

Product Overview

The MSCSM120TLM31C3AG device is a 1200V/89A three level inverter silicon carbide (SiC) MOSFET power module.





Note:

- 1. All ratings at $T_J = 25$ °C, unless otherwise specified.
- 2. All multiple inputs and outputs must be shorted together: 1/2/3; 10/11/12; 5/6/7/8; 21/22/23/24

⚠ CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM120TLM31C3AG device:

- SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
- SiC Schottky Diode (CR1 and CR2)
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Low stray inductance
- High level of integration
- AIN substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM120TLM31C3AG device:

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Application

The following are the applications of MSCSM120TLM31C3AG device:

· Uninterruptible power supplies

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120TLM31C3AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of MSCSM120TLM31C3AG device.

Table 1-1. Absolute Maximum Ratings

| Symbol | Parameter | | Maximum Ratings | Unit | |
|---------------------|----------------------------|------------------------|-----------------|------|--|
| V _{DSS} | Drain-Source voltage | | 1200 | V | |
| I _D | 10 20 | | 89 | А | |
| | | | 71 | | |
| I _{DM} | Pulsed drain current | | 180 | | |
| V _{GSmax} | Gate-Source voltage | | -10/25 | V | |
| R _{DS(on)} | Drain-Source ON resistance | | 31 | mΩ | |
| P _D | Power dissipation | T _C = 25 °C | 395 | W | |

The following table lists the electrical characteristics of MSCSM120TLM31C3AG device.

Table 1-2. Electrical Characteristics

| Symbol | Characteristic | Test Conditions | | Min. | Тур. | Max. | Unit |
|---------------------|---------------------------------|---|------------------------|------|------|------|------|
| I _{DSS} | Zero gate voltage drain current | V _{GS} = 0V V _{DS} = 1200V | | _ | 10 | 100 | μΑ |
| R _{DS(on)} | Drain-Source on | V _{GS} = 20V | T _J = 25 °C | _ | 25 | 31 | mΩ |
| | resistance | $I_D = 40A$ $T_J = 175 °C$ | | _ | 40 | _ | |
| V _{GS(th)} | Gate threshold voltage | $V_{GS} = V_{DS}$ $I_D = 1 \text{ mA}$ | | 1.8 | 2.8 | _ | V |
| I _{GSS} | Gate–Source leakage current | V _{GS} = 20V V _{DS} = 0V | | _ | _ | 150 | nA |

The following table lists the dynamic characteristics of MSCSM120TLM31C3AG device.

Table 1-3. Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | | Min. | Тур. | Max. | Unit |
|---------------------|------------------------------|---|-------------------------|------|------|------|------|
| C _{iss} | Input capacitance | V _{GS} = 0V | | _ | 3020 | _ | pF |
| Coss | Output capacitance | V _{DS} = 1000V | | _ | 270 | _ | |
| C _{rss} | Reverse transfer capacitance | f = 1 MHz | | _ | 25 | _ | |
| Qg | Total gate charge | V _{GS} = -5V/20V | | _ | 232 | _ | nC |
| Qgs | Gate-Source charge | V _{Bus} = 800V | | _ | 41 | _ | |
| Qgd | Gate-Drain charge | I _D = 40A | | _ | 50 | _ | |
| T _{d(on)} | Turn-on delay time | V _{GS} = -5V/20V | | _ | 30 | _ | ns |
| Tr | Rise time | V _{Bus} = 800V | | _ | 30 | _ | |
| T _{d(off)} | Turn-off delay time | I _D = 50A | | _ | 50 | _ | |
| Tf | Fall time | $R_{Gon} = 8\Omega$ $R_{Goff} = 4.7\Omega$ | | | 25 | _ | |
| Eon | Turn-on energy | V _{GS} = -5V/20V | T _J = 150 °C | _ | 0.99 | _ | mJ |
| E _{off} | Turn-off energy | $V_{Bus} = 600V$ $I_{D} = 50A$ $R_{Gon} = 8\Omega$ $R_{Goff} = 4.7\Omega$ | TJ = 150 °C | _ | 0.66 | _ | |
| RGint | Internal gate resistance | | | _ | 0.88 | _ | Ω |
| RthJC | Junction-to-case thermal | resistance | | _ | _ | 0.38 | °C/W |

The following table lists the body diode ratings and characteristics of MSCSM120TLM31C3AG device.

Table 1-4. Body Diode Ratings and Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Тур. | Max. | Unit |
|-----------------|--------------------------|---------------------------------|------|------|------|------|
| V_{SD} | Diode forward voltage | V _{GS} = 0V | | 4 | _ | V |
| | | I _{SD} = 40A | | | | |
| | | V _{GS} = -5V | _ | 4.2 | _ | |
| | | I _{SD} = 40A | | | | |
| t _{rr} | Reverse recovery time | I _{SD} = 40A | _ | 90 | _ | ns |
| Q _{rr} | Reverse recovery charge | $V_{GS} = -5V$ | _ | 550 | _ | nC |
| Irr | Reverse recovery current | V _R = 800V | _ | 13.5 | _ | Α |
| | | di _F /dt = 1000 A/μs | | | | |

1.2 CR1 and CR2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the CR1 and CR2 SiC diode ratings and characteristics (per SiC diode) of MSCSM120TLM31C3AG device.

Table 1-5. CR1 and CR2 SiC Diode Ratings and Characteristics

| Symbol | Characteristic | Test Conditions | | Min. | Тур. | Max. | Unit |
|-------------------|--------------------------------------|-------------------------|-------------------------|------|------|------|------|
| V_{RRM} | Peak repetitive reverse vo | oltage | _ | _ | 1200 | V | |
| I _{RM} | Reverse leakage current | V _R = 1200 V | T _J = 25 °C | _ | 15 | 200 | μA |
| | | | T _J = 175 °C | _ | 250 | _ | |
| IF | DC forward current | T _C = 100 °C | | _ | 50 | _ | Α |
| V _F | V _F Diode forward voltage | I _F = 50 A | T _J = 25 °C | _ | 1.5 | 1.8 | V |
| | | | T _J = 175 °C | _ | 2.1 | _ | |
| Q _C | Total capacitive charge | V _R = 600 V | | _ | 224 | _ | nC |
| С | Total capacitance | capacitance f = 1 MHz — | _ | 246 | _ | pF | |
| | V _R = 400 V f = 1 MHz | | | | | | |
| | | | _ | 182 | _ | | |
| | | V _R = 800 V | | | | | |
| R _{thJH} | Junction-to-heatsink therr | mal resistance | | _ | _ | 0.56 | °C/W |

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120TLM31C3AG device.

Table 1-6. Thermal and Package Characteristics

| Symbol | Characteristic | Min. | Max. | Unit | | |
|-------------------|------------------------------------|------|-----------------------|------|-----|---|
| V _{ISOL} | RMS isolation voltage, any termina | 4000 | _ | V | | |
| T _J | Operating junction temperature ran | -40 | 175 | °C | | |
| T _{JOP} | Recommended junction temperatu | -40 | T _{Jmax} –25 | | | |
| T _{STG} | Storage case temperature | -40 | 125 | | | |
| T _C | Operating case temperature | -40 | 125 | | | |
| Torque | Mounting torque | 2 | 3 | N.m | | |
| Wt | Package weight | | | _ | 110 | g |

1.4 Typical SiC MOSFET Performance Curve (Per SiC MOSFET)

This section shows the typical SiC MOSFET performance curves of the MSCSM120TLM31C3AG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance

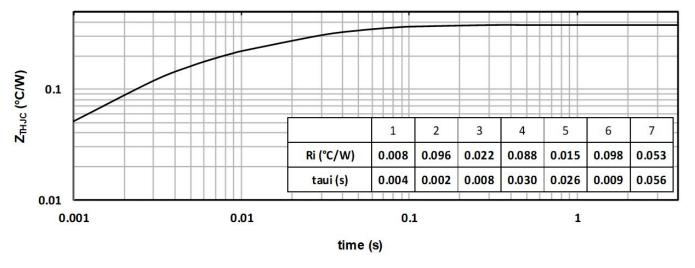
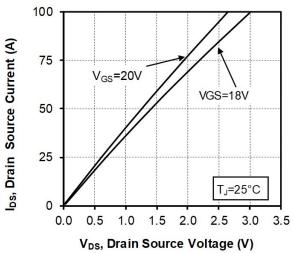


Figure 1-2. Output Characteristics, T_J = 25 °C



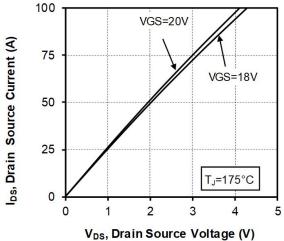


Figure 1-3. Output Characteristics, T_J = 175 °C

Figure 1-4. Normalized R_{DS(on)} vs. Temperature

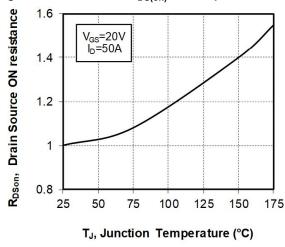


Figure 1-5. Transfer Characteristics

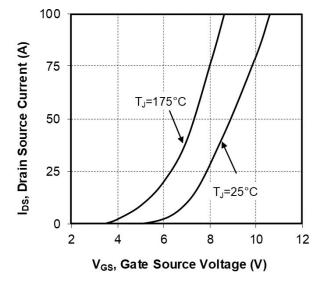


Figure 1-6. Switching Energy vs. Rg

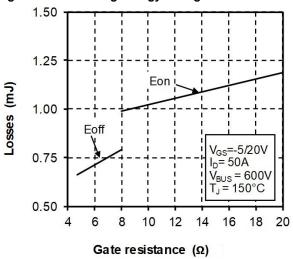


Figure 1-7. Switching Energy vs. Current

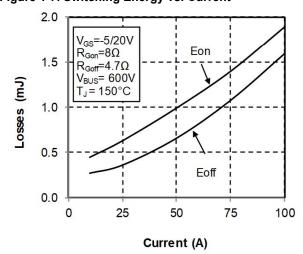


Figure 1-8. Capacitance vs. Drain Source Voltage

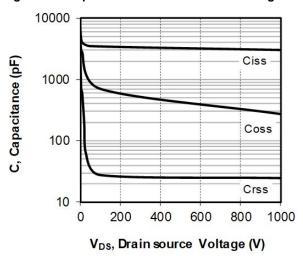
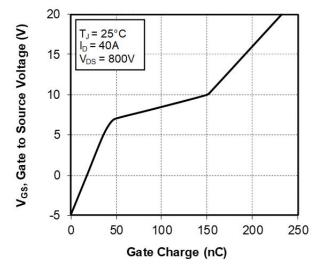
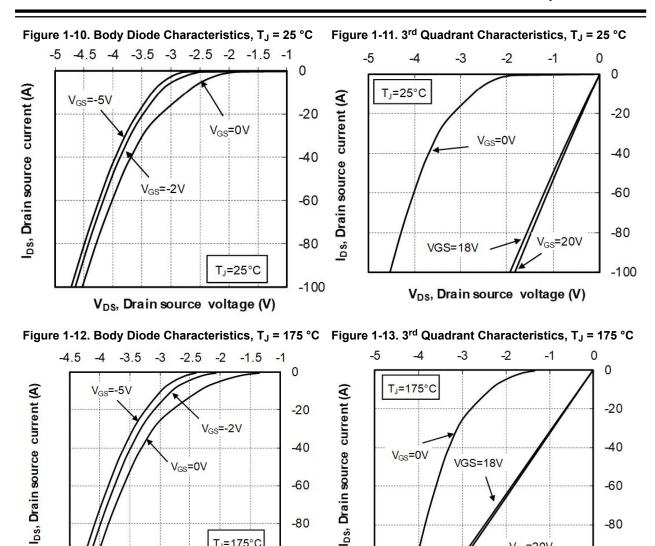


Figure 1-9. Gate Charge vs. Gate Source Voltage





-60

-80

-100

T_J=175°C

V_{DS}, Drain source voltage (V)

-60

-80

-100

V_{GS}=20V

V_{DS}, Drain source voltage (V)

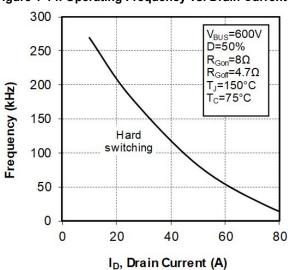


Figure 1-14. Operating Frequency vs. Drain Current

1.5 Typical SiC Diode Performance Curves (Per SiC Diode)

This section shows the typical SiC diode performance curves of the MSCSM120TLM31C3AG device.

Figure 1-15. Junction-to-Heatsink Thermal Impedance

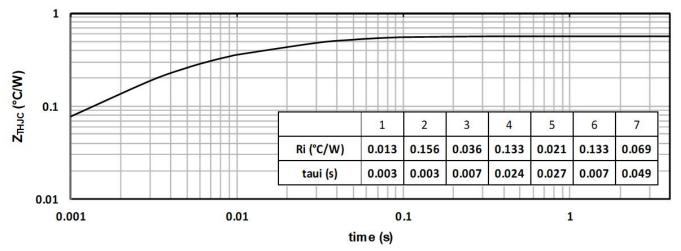


Figure 1-16. Forward Characteristics

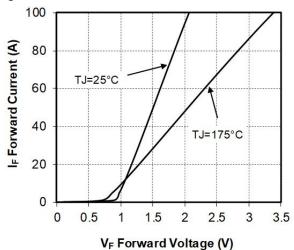
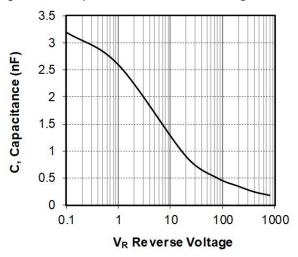


Figure 1-17. Capacitance vs. Reverse Voltage



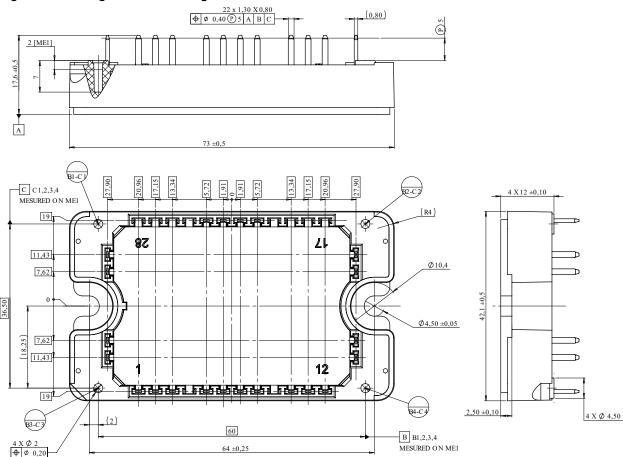
2. Package Specifications

The following section shows the package specification of the device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120TLM31C3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See application note AN3500A—Mounting instructions for SP1F and SP3F power modules.

MSCSM120TLM31C3AG

Revision History

3. Revision History

| Revision | Date | Description |
|----------|---------|------------------|
| Α | 12/2021 | Initial Revision |

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